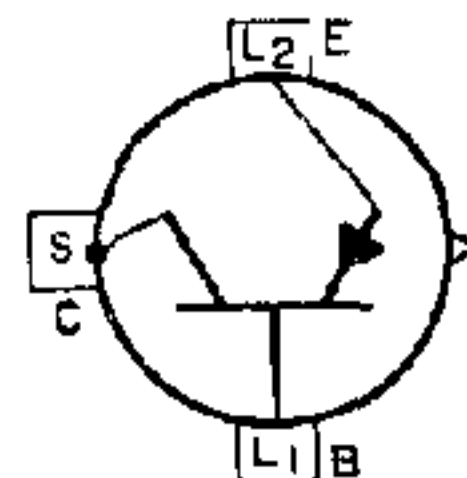


POWER TRANSISTOR

2N1358

Germanium p-n-p type used in a wide variety of switching and amplifier applications in industrial and military equipment requiring transistors having high voltage, current, and dissipation values. It is used in power-



switching, voltage- and current-regulating, dc-to-dc converter, inverter, power-supply, and relay- and solenoid-actuating circuits; and in low-frequency oscillator and audio-amplifier service. This type is designed to provide satisfactory performance under extreme environmental conditions of temperature, moisture, and altitude; it is stud-mounted to provide positive heat-sink contact, and has a cold-weld seal to insure reliable performance under severe environmental conditions. JEDEC No. TO-36 package; outline 14, Outlines Section. This type is identical with type 2N174 except for the following items:

CHARACTERISTICS

Collector-to-Emitter Breakdown Voltage:

With base short-circuited to emitter and collector amperes = -0.3	-70 min	volts
With base open and collector amperes = -0.3	-40 min	volts

Base-to-Emitter Voltage:

With collector-to-emitter volts = -2 and collector amperes = -5	-0.65	volt
With collector-to-base volts = -2 and collector amperes = -1.2	-0.35	volt

Emitter-to-Base Voltage (with collector-to-base volts = -80 and emitter current = 0)	-0.15	volt
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Emitter-Cutoff Current (with emitter-to-base volts = -60 and collector current = 0)	-1	ma
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Collector-Cutoff Current (with collector-to-base volts = -2 and emitter current = 0)	-100	μa
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In Common-Base Circuit

Small-Signal Forward-Current-Transfer-Ratio Cutoff Frequency (with collector-to-base volts = -12 and collector amperes = -1)	100	kc
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In Common-Emitter Circuit

DC Forward Current-Transfer Ratio:

With collector-to-emitter volts = -2 and collector amperes = -1.2	55
With collector-to-emitter volts = -2 and collector amperes = -5	35